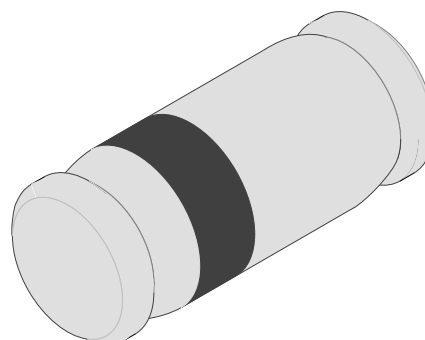




Switching Diode

Features

- Silicon Epitaxial Planar Diodes



94 9371

Applications

General purposes

Order Instruction

Type	Type Differentiation	Ordering Code	Remarks
BAV100	$V_{RRM} = 60\text{ V}$	BAV100-GS08	Tape and Reel
BAV101	$V_{RRM} = 120\text{ V}$	BAV101-GS08	Tape and Reel
BAV102	$V_{RRM} = 200\text{ V}$	BAV102-GS08	Tape and Reel
BAV103	$V_{RRM} = 250\text{ V}$	BAV103 -GS08	Tape and Reel

Absolute Maximum Ratings

 $T_j = 25^\circ\text{C}$

Parameter	Test Conditions	Type	Symbol	Value	Unit
Repetitive peak reverse voltage		BAV100	V_{RRM}	60	V
		BAV101	V_{RRM}	120	V
		BAV102	V_{RRM}	200	V
		BAV103	V_{RRM}	250	V
Reverse voltage		BAV100	V_R	50	V
		BAV101	V_R	100	V
		BAV102	V_R	150	V
		BAV103	V_R	200	V
Peak forward surge current	$t_p=1\text{ s}$		I_{FSM}	1	A
Repetitive peak forward current			I_{FRM}	625	mA
Forward current			I_F	250	mA
Power dissipation			P_V	500	mW
Junction temperature			T_j	175	$^\circ\text{C}$
Storage temperature range			T_{stg}	-65...+175	$^\circ\text{C}$

Maximum Thermal Resistance

 $T_j = 25^\circ\text{C}$

Parameter	Test Conditions	Symbol	Value	Unit
Junction lead		R_{thJL}	350	K/W
Junction ambient	on PC board 50 mmx50 mmx1.6 mm	R_{thJA}	500	K/W

Electrical Characteristics

 $T_j = 25^\circ\text{C}$

Parameter	Test Conditions	Type	Symbol	Min	Typ	Max	Unit
Forward voltage	$I_F=100\text{mA}$		V_F			1	V
Reverse current	$V_R=50\text{ V}$	BAV100	I_R			100	nA
	$V_R=100\text{ V}$	BAV101	I_R			100	nA
	$V_R=150\text{ V}$	BAV102	I_R			100	nA
	$V_R=200\text{ V}$	BAV103	I_R			100	nA
	$T_j=100^\circ\text{C}$, $V_R=50\text{ V}$	BAV100	I_R			15	μA
	$T_j=100^\circ\text{C}$, $V_R=100\text{ V}$	BAV101	I_R			15	μA
	$T_j=100^\circ\text{C}$, $V_R=150\text{ V}$	BAV102	I_R			15	μA
	$T_j=100^\circ\text{C}$, $V_R=200\text{ V}$	BAV103	I_R			15	μA
Breakdown voltage	$I_R=100\mu\text{A}$, $t_p/T=0.01$, $t_p=0.3\text{ms}$	BAV100	$V_{(BR)}$	60			V
		BAV101	$V_{(BR)}$	120			V
		BAV102	$V_{(BR)}$	200			V
		BAV103	$V_{(BR)}$	250			V
Diode capacitance	$V_R=0$, $f=1\text{MHz}$		C_D		1.5		pF
Differential forward resistance	$I_F=10\text{mA}$		r_f		5		Ω
Reverse recovery time	$I_F=I_R=30\text{mA}$, $i_R=3\text{mA}$, $R_L=100\Omega$		t_{rr}			50	ns

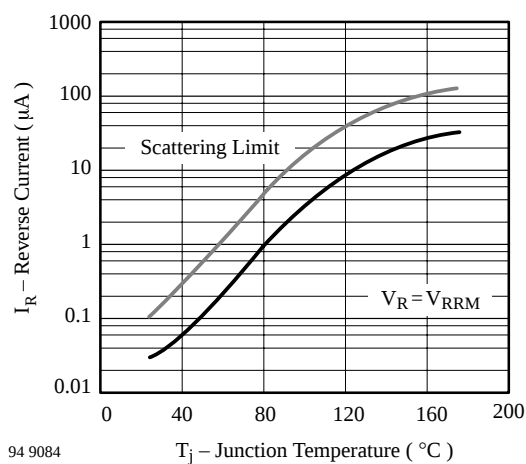
Characteristics ($T_j = 25^\circ\text{C}$ unless otherwise specified)

Figure 1. Reverse Current vs. Junction Temperature

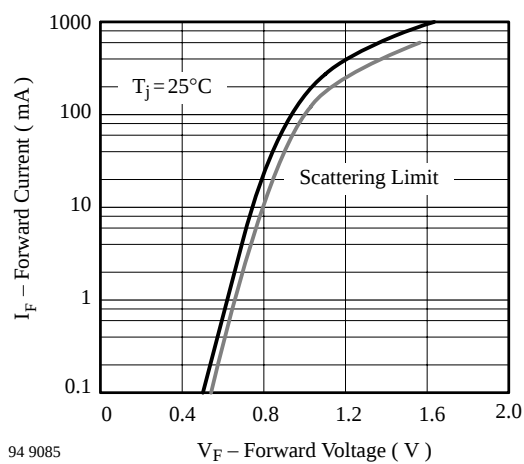


Figure 2. Forward Current vs. Forward Voltage

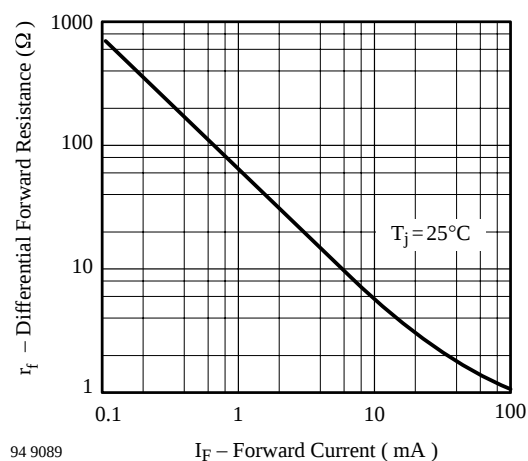
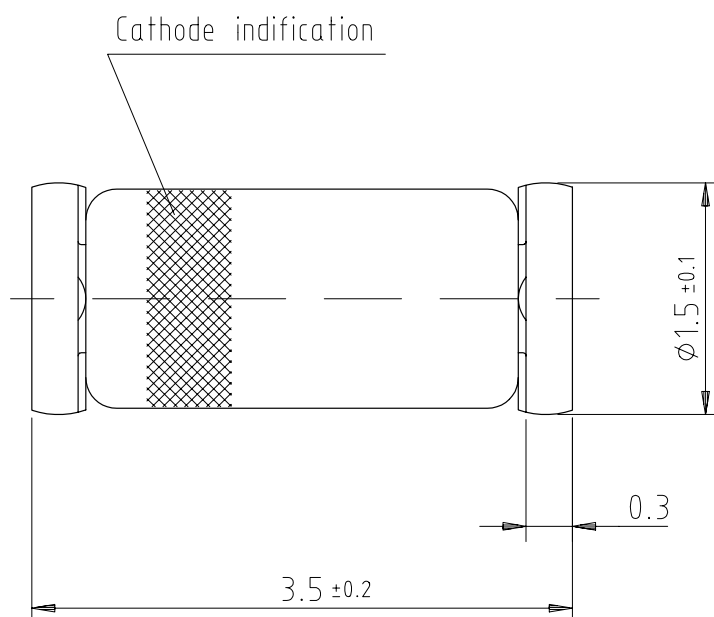


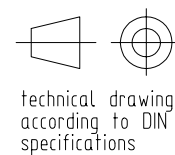
Figure 3. Differential Forward Resistance vs. Forward Current

Dimensions in mm



Glass case
Mini MELF / SOD 80
JEDEC DO 213 AA

96 12070



technical drawings
according to DIN
specifications

Ozone Depleting Substances Policy Statement

It is the policy of **Vishay Semiconductor GmbH** to

1. Meet all present and future national and international statutory requirements.
2. Regularly and continuously improve the performance of our products, processes, distribution and operating systems with respect to their impact on the health and safety of our employees and the public, as well as their impact on the environment.

It is particular concern to control or eliminate releases of those substances into the atmosphere which are known as ozone depleting substances (ODSs).

The Montreal Protocol (1987) and its London Amendments (1990) intend to severely restrict the use of ODSs and forbid their use within the next ten years. Various national and international initiatives are pressing for an earlier ban on these substances.

Vishay Semiconductor GmbH has been able to use its policy of continuous improvements to eliminate the use of ODSs listed in the following documents.

1. Annex A, B and list of transitional substances of the Montreal Protocol and the London Amendments respectively
2. Class I and II ozone depleting substances in the Clean Air Act Amendments of 1990 by the Environmental Protection Agency (EPA) in the USA
3. Council Decision 88/540/EEC and 91/690/EEC Annex A, B and C (transitional substances) respectively.

Vishay Semiconductor GmbH can certify that our semiconductors are not manufactured with ozone depleting substances and do not contain such substances.

We reserve the right to make changes to improve technical design and may do so without further notice.

Parameters can vary in different applications. All operating parameters must be validated for each customer application by the customer. Should the buyer use Vishay-Telefunken products for any unintended or unauthorized application, the buyer shall indemnify Vishay-Telefunken against all claims, costs, damages, and expenses, arising out of, directly or indirectly, any claim of personal damage, injury or death associated with such unintended or unauthorized use.

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